

80V, 242A, 2.1mΩ N-channel Power SGT MOSFET

JBL083M

Features

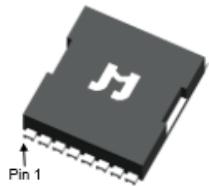
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% ΔV_{ds} Tested
- Halogen-free; RoHS-compliant

Applications

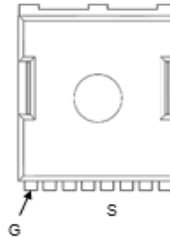
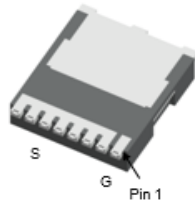
- Load Switch
- PWM Application
- Power Management

Product Summary

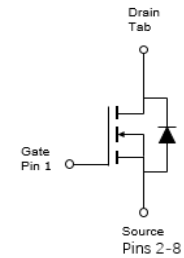
Parameters	Value	Unit
V_{DSS}	80	V
$V_{GS(th_Typ)}$	3.1	V
$I_D(@V_{GS}=10V)$	242	A
$R_{DS(ON_Typ)}(@V_{GS}=10V)$	2.1	mΩ



PowerJE®10x12



Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JBL083M	BL083M	1	Tape&Reel	PowerJE®10x12	2000	10000

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-to-Source Voltage	80	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	242
		$T_C = 100^\circ\text{C}$	171
I_{DM}	Pulsed Drain Current ⁽¹⁾	Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	900	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	286
		$T_C = 100^\circ\text{C}$	114
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	34	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.4	



**Electrical Characteristics** ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	80	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 64\text{V}$, $V_{GS} = 0\text{V}$	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	2.2	3.1	4.3	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance ⁽⁴⁾	$V_{GS} = 10\text{V}$, $I_D = 20\text{A}$	-	2.1	2.9	m Ω
Dynamic Characteristics						
R_g	Gate Resistance	$f = 1\text{MHz}$	-	0.8	-	Ω
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$, $V_{DS} = 40\text{V}$, $f = 1\text{MHz}$	4569	6396	8635	pF
C_{oss}	Output Capacitance		874	1224	1652	pF
C_{rss}	Reverse Transfer Capacitance		17	23	32	pF
Q_g	Total Gate Charge	$V_{GS} = 0$ to 10V $V_{DS} = 40\text{V}$, $I_D = 20\text{A}$	65	91	123	nC
Q_{gs}	Gate Source Charge		23	33	44	nC
Q_{gd}	Gate Drain ("Miller") Charge		13	18	24	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = 10\text{V}$, $V_{DD} = 40\text{V}$ $I_D = 20\text{A}$, $R_{GEN} = 6.2\Omega$	-	31	-	ns
t_r	Turn-On Rise Time		-	35	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	61	-	ns
t_f	Turn-Off Fall Time		-	31	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	242	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	967	A
V_{SD}	Body Diode Forward Voltage	$V_{GS} = 0\text{V}$, $I_S = 20\text{A}$	-		1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F = 20\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$	54	75	101	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	155	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 40\text{V}$, $V_G = 10\text{V}$, $R_G = 25\text{ohm}$, $L = 3\text{mH}$, $I_{AS} = 24.5\text{A}$, $V_{DD} = 0\text{V}$ during time in avalanche.
 3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.
 4. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.



Typical Performance Characteristics

Figure 1: Power De-rating

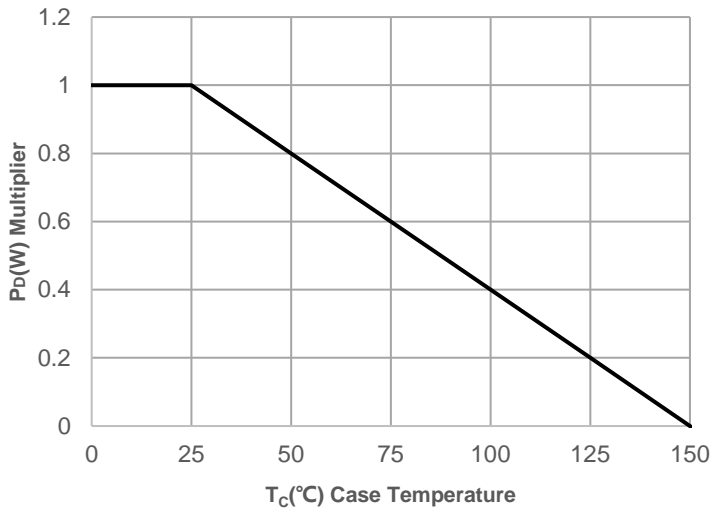


Figure 2: Current De-rating

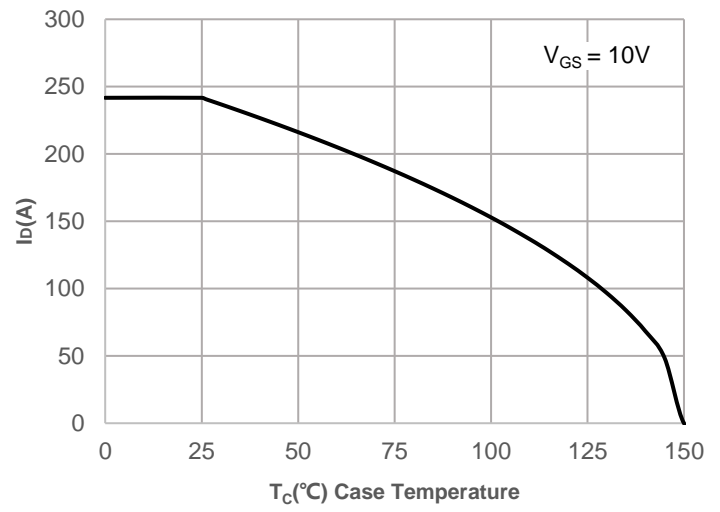


Figure 3: Normalized Maximum Transient Thermal Impedance

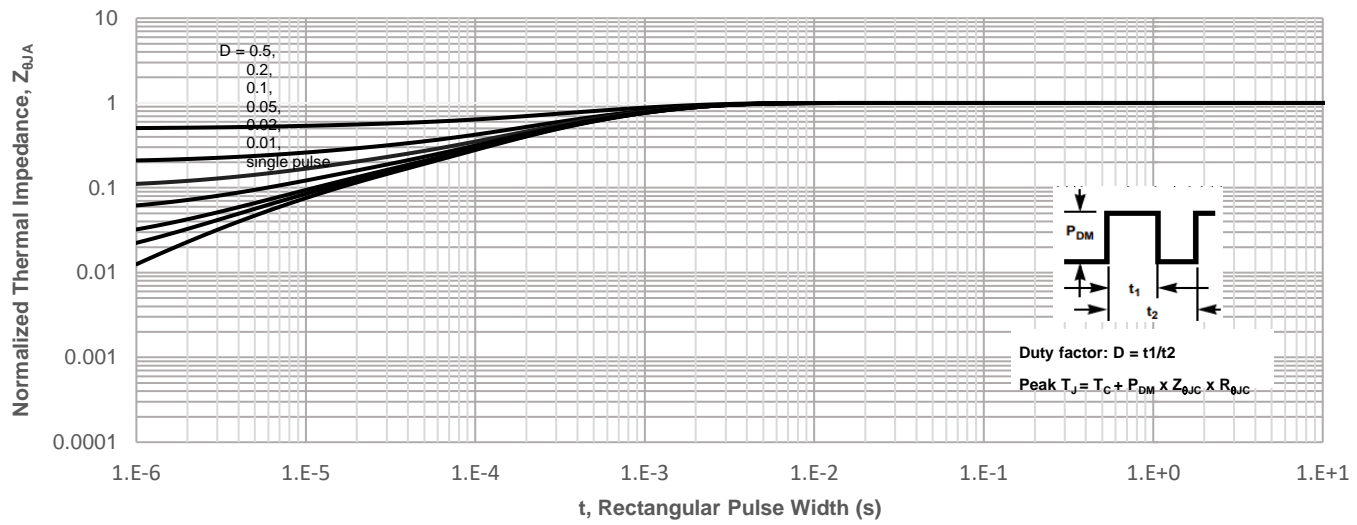
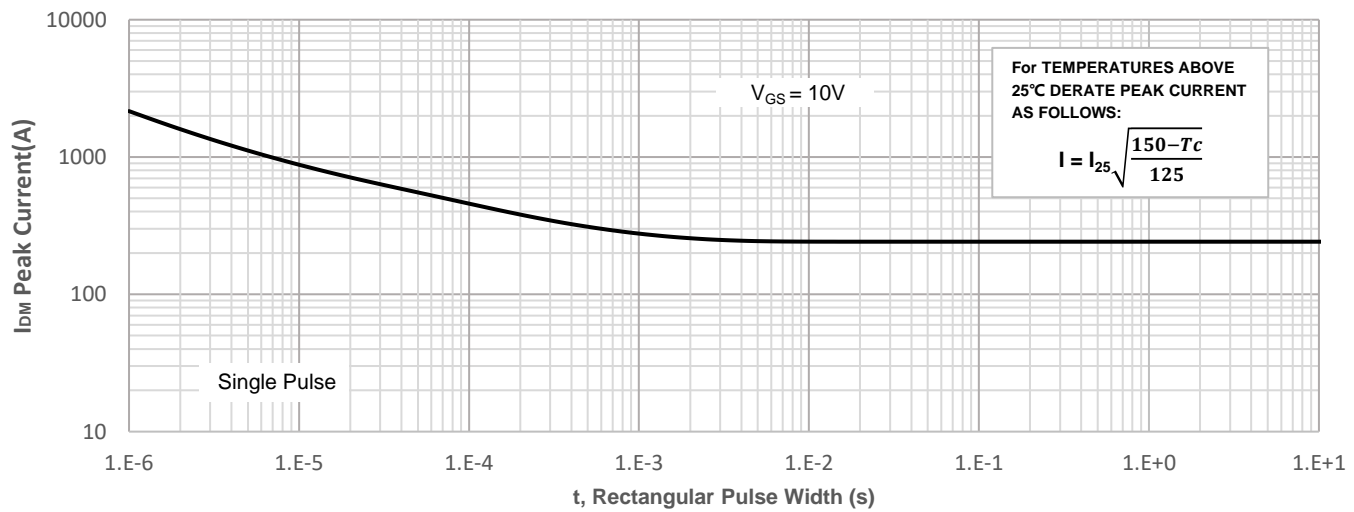
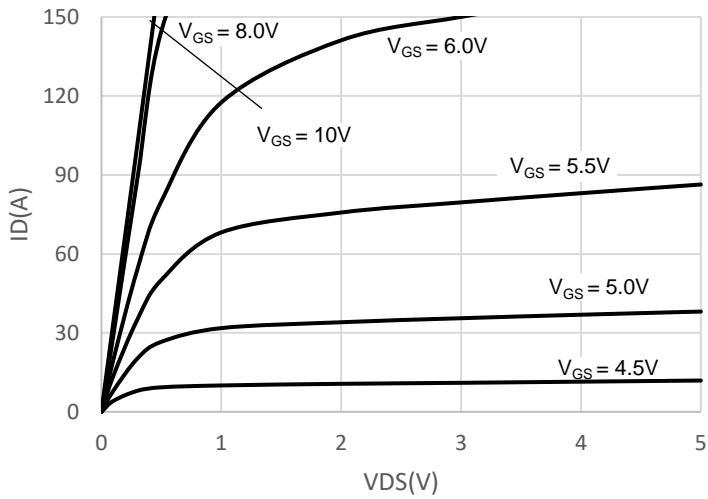
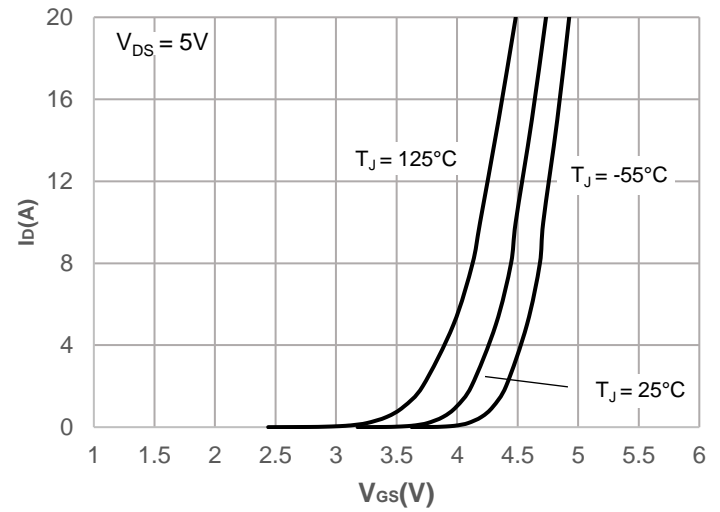
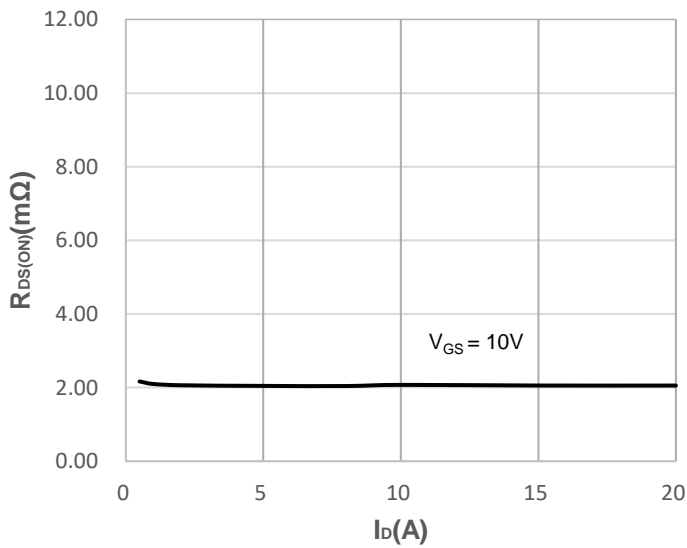
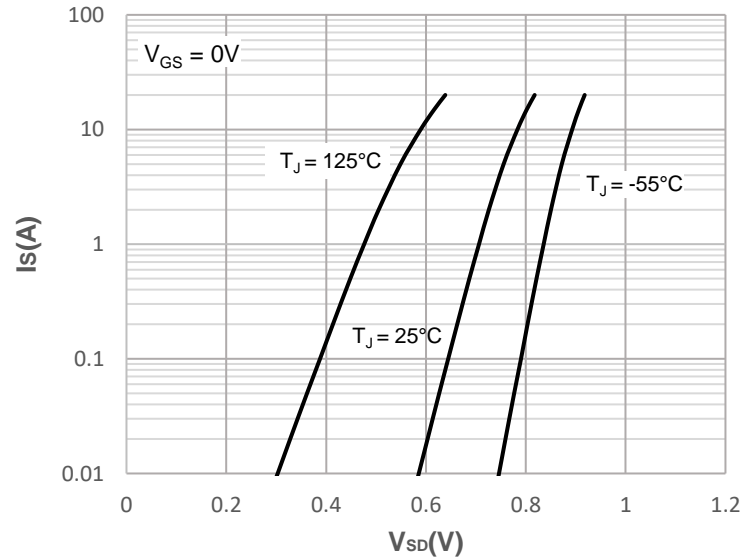
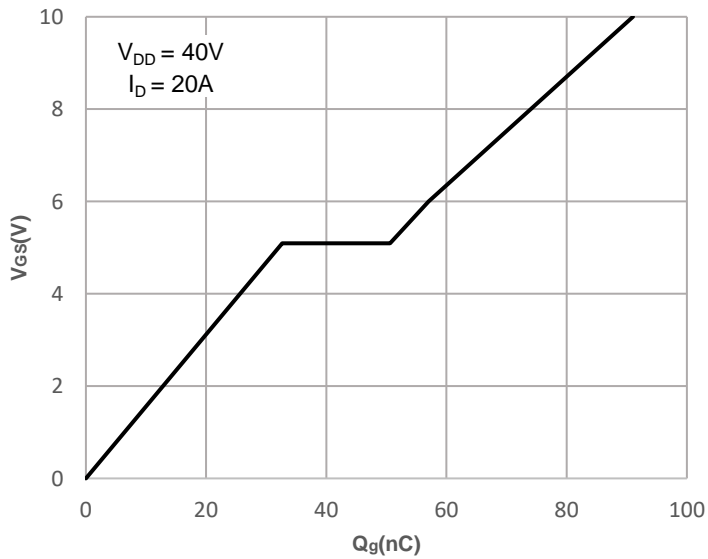
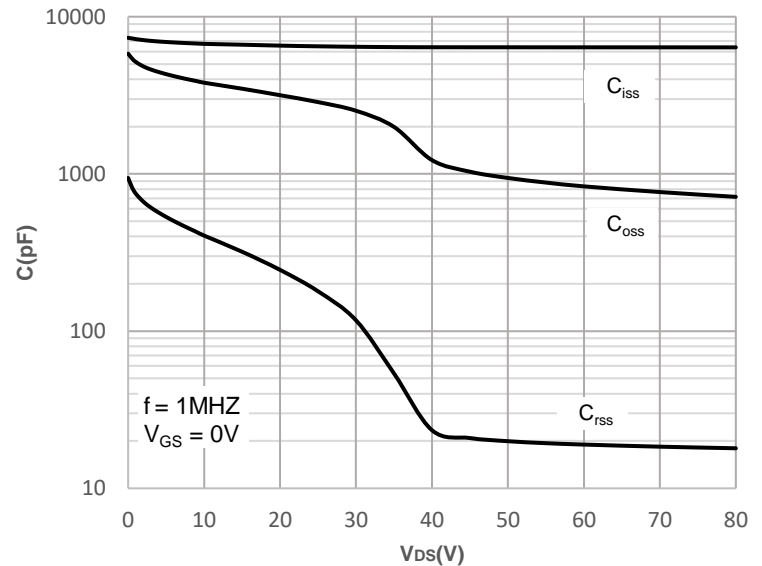


Figure 4: Peak Current Capacity



Typical Performance Characteristics

Figure 5: Output Characteristics

Figure 6: Typical Transfer Characteristics

Figure 7: On-resistance vs. Drain Current

Figure 8: Body Diode Characteristics

Figure 9: Gate Charge Characteristics

Figure 10: Capacitance Characteristics


Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

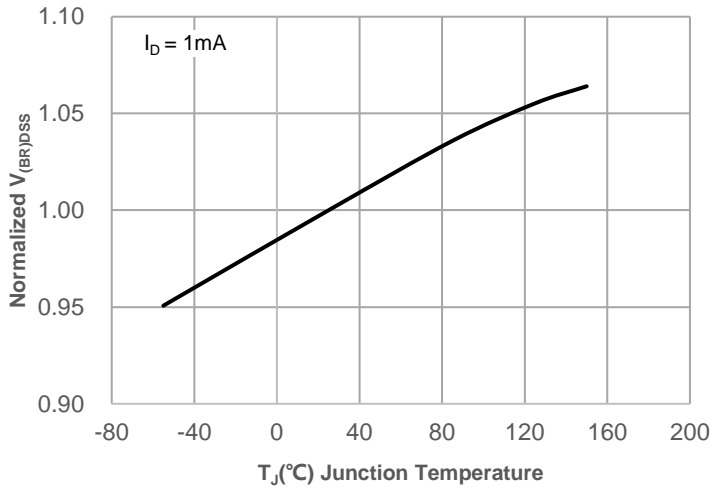


Figure 12: Normalized on Resistance vs. Junction Temperature

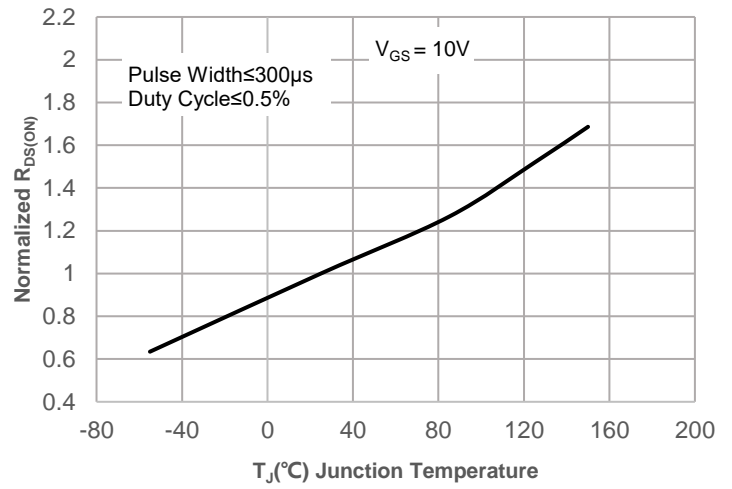


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

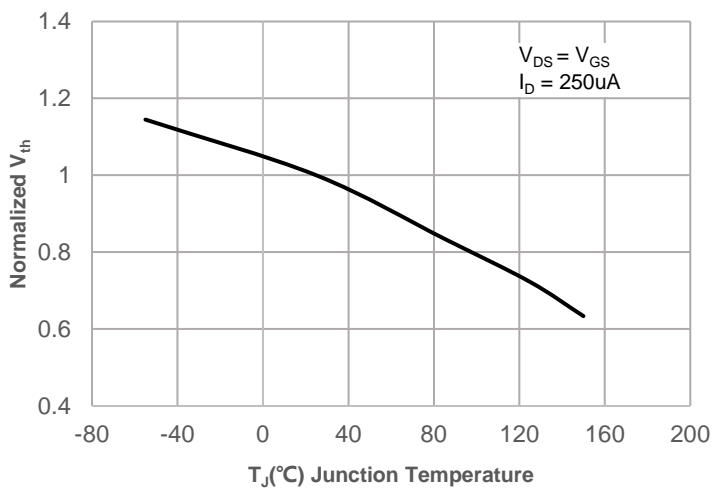


Figure 14: R_DS(ON) vs. V_GS

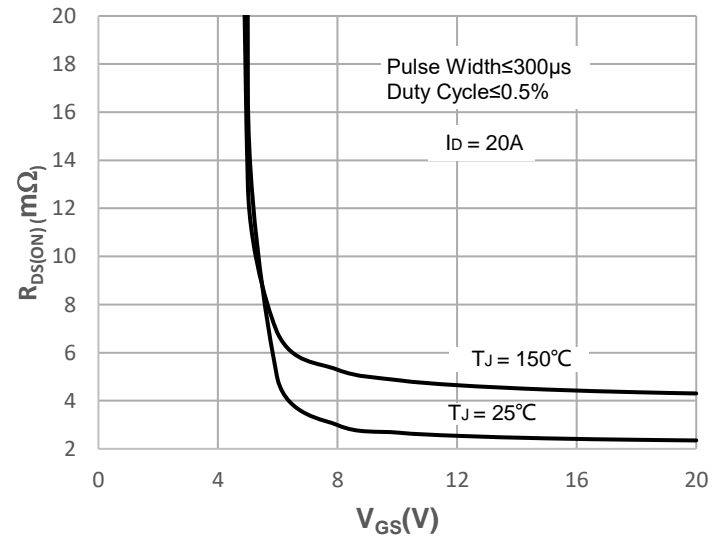
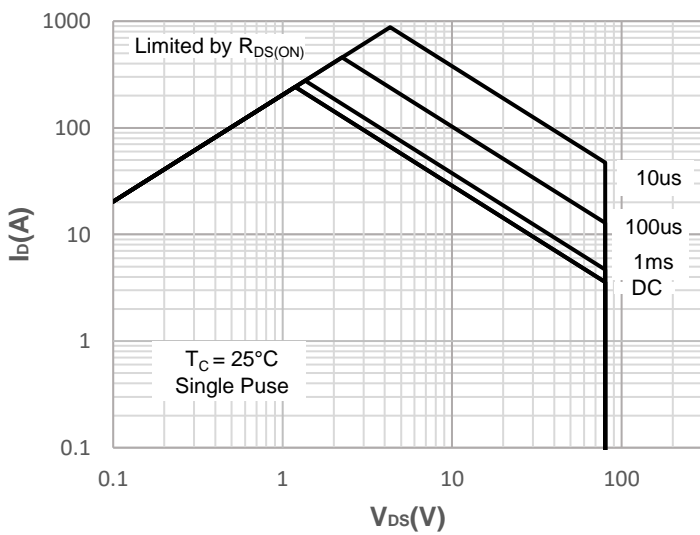


Figure 15: Maximum Safe Operating Area



Test Circuit

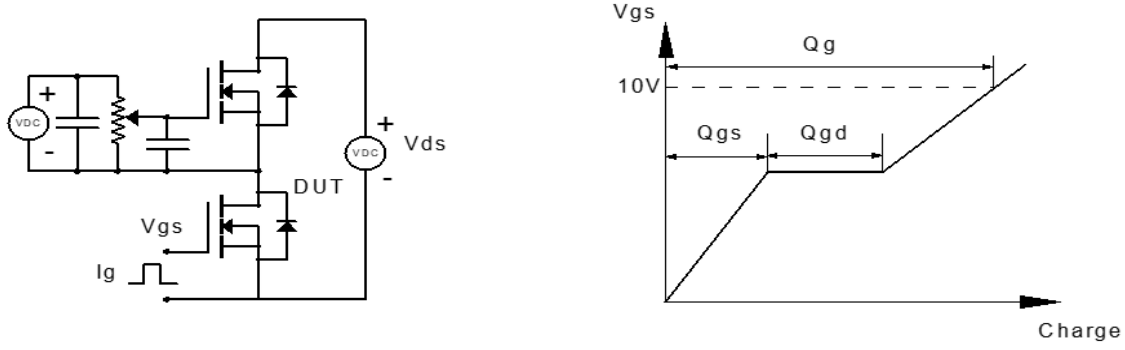


Figure 1: Gate Charge Test Circuit & Waveform

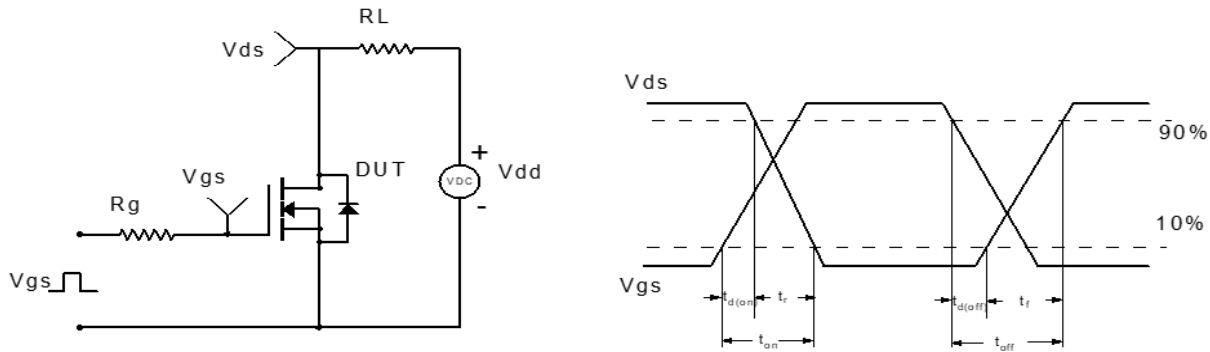


Figure 2: Resistive Switching Test Circuit & Waveform

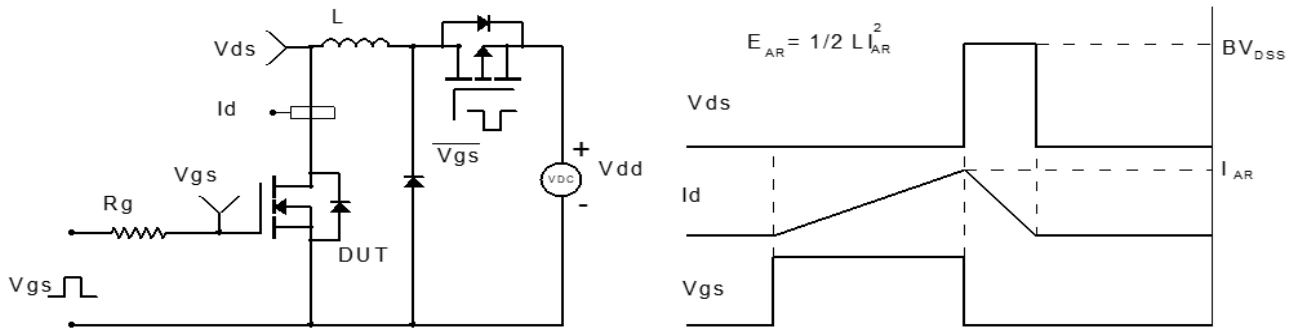


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

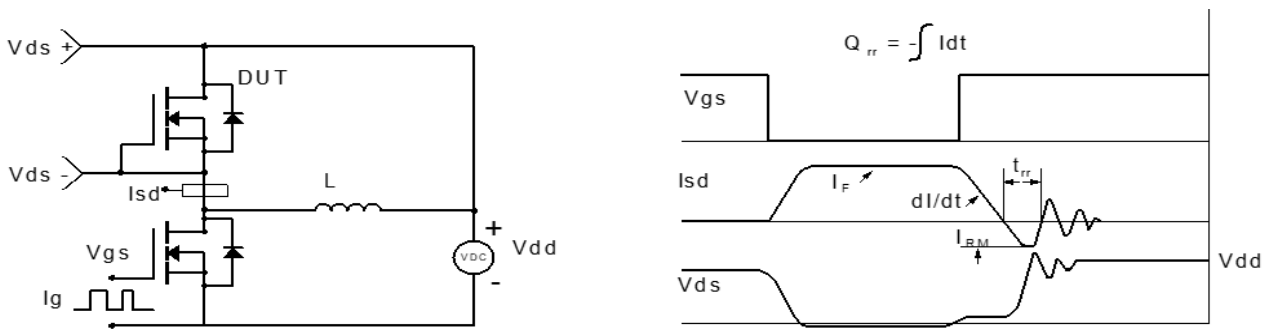
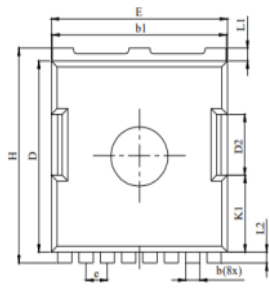
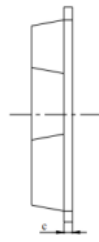
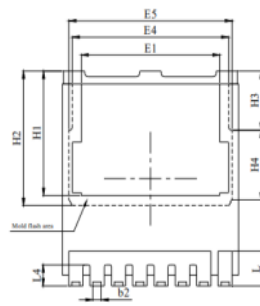
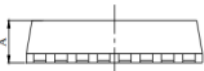


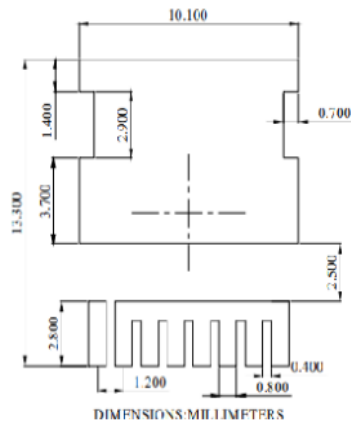
Figure 4: Diode Recovery Test Circuit & Waveform



Package Mechanical Data(PowerJE®10x12)

Package Outlines

Top View

Side View

Bottom View

Front View
NOTES:

1. Dimension and tolerance per ASME Y14.5M, 1994.
2. All dimensions in millimeter.
3. Dimensions do not include burrs or mold flash. Mold flash or burrs does not exceed 0.150mm.

Recommended Soldering Footprint


DIM.	MILLIMETER		
	MIN	NOM	MAX
A	2.20	2.30	2.50
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.42	0.46	0.50
C	0.40	0.50	0.65
D	10.28	10.38	10.58
D2	3.30		
E	9.70	9.90	10.10
E1	7.80		
E4	8.80		
E5	9.20		
e	1.20(BSC)		
H	11.48	11.68	11.88
H1	6.55	6.75	6.85
H2	7.30		
H3	3.20		
H4	3.80		
K1	4.18		
L	1.70	1.90	2.10
L1	0.70		
L2	0.60		
L4	1.00	1.15	1.30

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